

Silicon NPN Power Transistors

BD239/A/B/C

DESCRIPTION

With TO-220C package

·Complement to type BD240/A/B/C

APPLICATIONS

·For medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

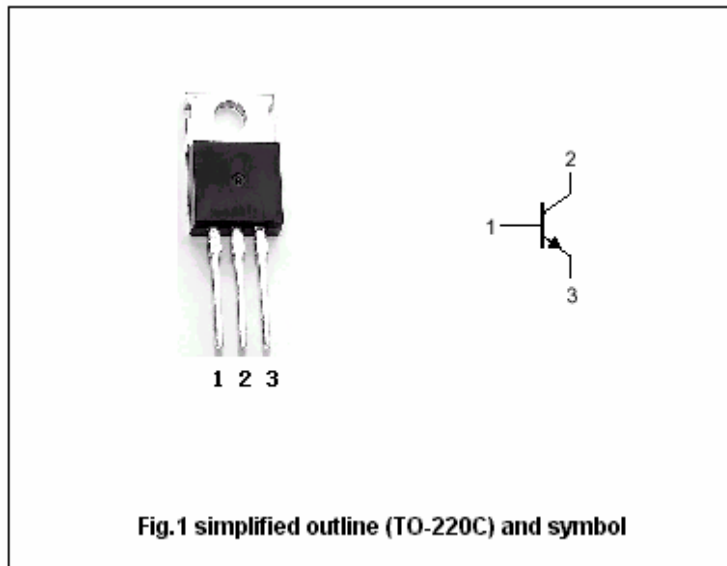


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	BD239	55	V
		BD239A	70	
		BD239B	90	
		BD239C	115	
V _{CEO}	Collector-emitter voltage	BD239	45	V
		BD239A	60	
		BD239B	80	
		BD239C	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		2	A
I _{CM}	Collector current-peak		4	A
I _B	Base current		0.6	A
P _C	Collector power dissipation	T _C =25°C	30	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-65~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BD239	45			V	
		BD239A	60				
		BD239B	80				
		BD239C	100				
V _{CEsat}	Collector-emitter saturation voltage	I _C =1 A; I _B =0.2 A			0.7	V	
V _{BE}	Base-emitter on voltage	I _C =1 A; V _{CE} =4V			1.3	V	
I _{CEO}	Collector cut-off current	BD239/A	V _{CE} =30V; I _B =0			0.3	mA
		BD239B/C	V _{CE} =60V; I _B =0				
I _{CES}	Collector cut-off current	BD239	V _{CE} =45V; V _{BE} =0			0.2	mA
		BD239A	V _{CE} =60V; V _{BE} =0				
		BD239B	V _{CE} =80V; V _{BE} =0				
		BD239C	V _{CE} =100V; V _{BE} =0				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA	
h _{FE-1}	DC current gain	I _C =0.2A; V _{CE} =4V	40				
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =4V	15				

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PACKAGE OUTLINE

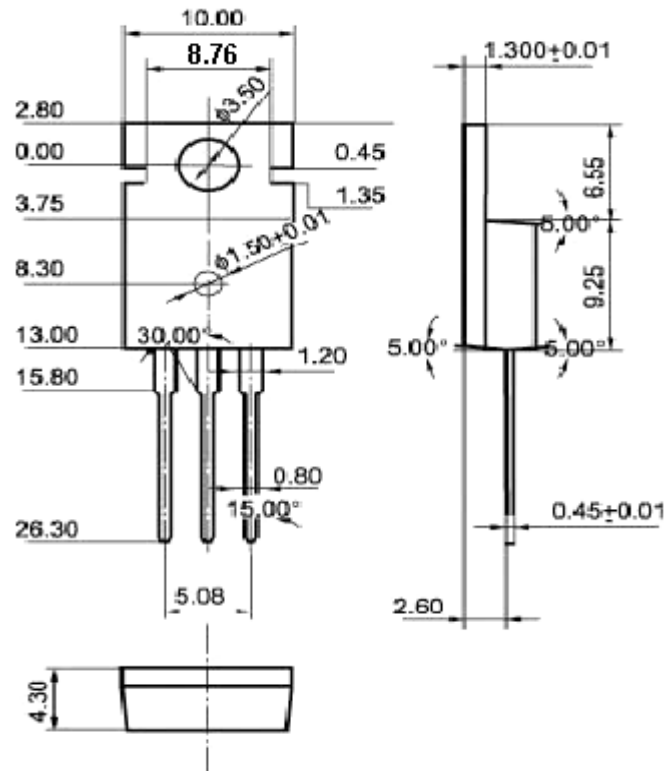


Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)